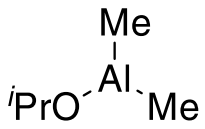
Catalog # 13-1600 Dimethylaluminum i-propoxide, 98% (99.99+%-Al) PURATREM



Thermal Behavior:

- Boiling point: 186°C [1], 172°C [8]
- Decomposition at ~370°C [8]
- Vapor pressure: 9 Torr/66.5°C [8]
- TGA data and diagram are available in [2, 8]

Technical Notes:

1. ALD precursor and dopant for aluminum containing film deposition.

Target Deposit	Deposition Technique	Delivery Temperature	Pressure	Co-reactants	Deposition Temperature	Ref.
Al_2O_3	ALD ALD AS-ALD PE-ALD PE-ALD	85-90°C 60°C 60°C 90°C 90°C	3 Torr - - - -	H_2O H_2O H_2O $^{PL}O_2$ $^{PL}O_2$	100-250°C, 150°C 120°C 50-250°C 25-250°C 25-350°C	2-4 5 6, 7 8 9
In:Al_2O_3	PE-ALD	50°C	1-1.11 Torr	$Et_2InN(TMS)_2$, $^{PL}O_2$	250°C	10
Al:ZnO_2	ALD	90°C	-	Et_2Zn, H_2O	250°C	12

References:

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